FAIRCHILD SEMICONDUCTOR®

February 2006

# FDS5692Z

## N-Channel UltraFET Trench® MOSFET

### 50V, 5.8A, 24mΩ

### General Description

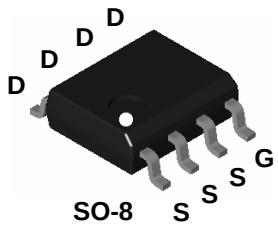
This N-Channel UltraFET device has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $r_{DS(on)}$ and fast switching speed.

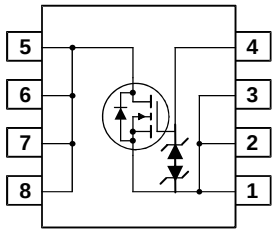
### Applications

- DC/DC converter

### Features

- Max $r_{DS(on)}$ = 24mΩ at $V_{GS}$ = 10V, $I_D$ = 5.8A
- Max $r_{DS(on)}$ = 33mΩ at $V_{GS}$ = 4.5V, $I_D$ = 5.6A
- ESD protection diode (note 3)
- Low Qgd
- Fast switching speed




## MOSFET Maximum Ratings $T_A$=25°C unless otherwise noted

| Symbol | Parameter | | Ratings | Units |
|---|---|---|---|---|
| $V_{DS}$ | Drain-Source Voltage | | 50 | V |
| $V_{GS}$ | Gate-Source Voltage | | ± 20 | V |
| $I_D$ | Drain Current – Continuous | (Note 1a) | 5.8 | A |
| | – Pulsed | | 40 | |
| $E_{AS}$ | Single Pulse Avalanche Energy | | 72 | mJ |
| $P_D$ | UltraFET Dissipation for Single Operation | (Note 1a) | 2.5 | W |
| | | (Note 1b) | 1.2 | |
| | | (Note 1c) | 1.1 | |
| $T_J$, $T_{STG}$ | Operating and Storage Junction Temperature Range | | –55 to 150 | °C |

## Thermal Characteristics

| | | | | |
|---|---|---|---|---|
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | (Note 1a) | 50 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | (Note 1c) | 125 | |
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case | (Note 1) | 25 | |

## Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape width | Quantity |
|---|---|---|---|---|---|
| FDS5692Z | FDS5692Z | SO-8 | 13” | 12mm | 2500units |

## Electrical Characteristics

$T_A$ = 25°C unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|---|---|---|---|---|---|---|
| **Drain-Source Avalanche Ratings** | | | | | | |
| $E_{AS}$ | Drain-Source Avalanche Energy (Single Pulse) | $V_{DD}$ = 50 V, $I_D$= 12 A, L=1mH | | | 72 | mJ |
| $I_{AS}$ | Drain-Source Avalanche Current | | | 12 | | A |
| **Off Characteristics** | | | | | | |
| $BV_{DSS}$ | Drain–Source Breakdown Voltage | $V_{GS}$ = 0 V, $I_D$ = 250 μA | 50 | | | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D$ = 250 μA, Referenced to 25°C | | 48 | | mV/°C |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$ = 40 V $V_{GS}$ = 0 V | | | 1 | μA |
| $I_{GSS}$ | Gate–Body Leakage | $V_{GS}$ = ± 20V, $V_{DS}$ = 0 V | | | ± 10 | μA |
| **On Characteristics** (Note 4) | | | | | | |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}$ = $V_{GS}$, $I_D$ = 250 μA | 1 | 1.6 | 3 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate Threshold Voltage Temperature Coefficient | $I_D$ = 250 μA, Referenced to 25°C | | –6 | | mV/°C |
| $r_{DS(on)}$ | Static Drain–Source On–Resistance | $V_{GS}$ = 10 V, $I_D$ = 5.8 A<br>$V_{GS}$ = 4.5 V, $I_D$ = 5.6 A<br>$V_{GS}$ = 10 V, $I_D$ = 5.8A, $T_J$ = 125°C | | 20<br>26<br>32 | 24<br>33<br>41 | mΩ |
| **Dynamic Characteristics** | | | | | | |
| $C_{iss}$ | Input Capacitance | $V_{DS}$ = 25 V, $V_{GS}$ = 0 V, f = 1.0 MHz | | 1025 | | pF |
| $C_{oss}$ | Output Capacitance | | | 150 | | pF |
| $C_{rss}$ | Reverse Transfer Capacitance | | | 50 | | pF |
| $R_G$ | Gate Resistance | f = 1.0 MHz | | 0.79 | | Ω |
| $Q_{g(TOT)}$ | Total Gate Charge, $V_{GS}$ = 10V | $V_{DS}$ = 25V, $I_D$ = 5.8A | | 18 | 25 | nC |
| $Q_{g(TOT)}$ | Total Gate Charge, $V_{GS}$ = 5V | | | 10 | 14 | nC |
| $Q_{gs}$ | Gate–Source Gate Charge | | | 2.8 | | nC |
| $Q_{gd}$ | Gate–Drain Gate Charge | | | 3.0 | | nC |
| **Switching Characteristics** (Note 4) | | | | | | |
| $t_{d(on)}$ | Turn–On Delay Time | $V_{DD}$ = 25 V, $I_D$ = 5.8A, $V_{GS}$ = 10 V, $R_{GEN}$ = 6 Ω | | 9 | 18 | ns |
| $t_r$ | Rise Time | | | 5 | 10 | ns |
| $t_{d(off)}$ | Turn–Off Delay Time | | | 27 | 43 | ns |
| $t_f$ | Fall Time | | | 6 | 12 | ns |

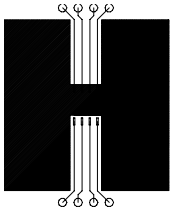
## Electrical Characteristics

$T_A$ = 25°C unless otherwise noted

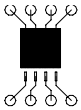
| Symbol | Parameter | Test Conditions | | Min | Typ | Max | Units |
|---|---|---|---|---|---|---|---|
| **Drain–Source Diode Characteristics** | | | | | | | |
| $V_{SD}$ | Drain–Source Diode Forward Voltage | $V_{GS}$ = 0 V, | $I_S$ = 5.8 A | | 0.79 | 1.25 | V |
| | | | $I_S$ = 2.9 A | | 0.75 | 1.0 | V |
| $t_{rr}$ | Reverse Recovery Time | $I_F$ = 6A, $dI_F/dt$ = 100A/µs | | | 24 | | ns |
| $Q_{rr}$ | Reverse Recovery Charge | | | | 16 | | nC |

**Notes:**

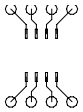
**1.** $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 50°C/W when mounted on a 1in$^2$ pad of 2 oz copper



b) 105°C/W when mounted on a .04 in$^2$ pad of 2 oz copper



c) 125°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

**2.** Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%

**3.** The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

## Typical Characteristics

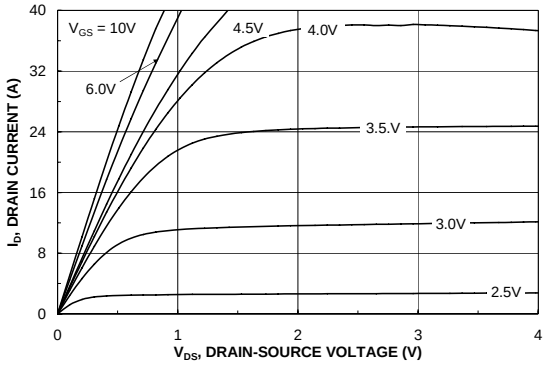



**Figure 1. On-Region Characteristics.**

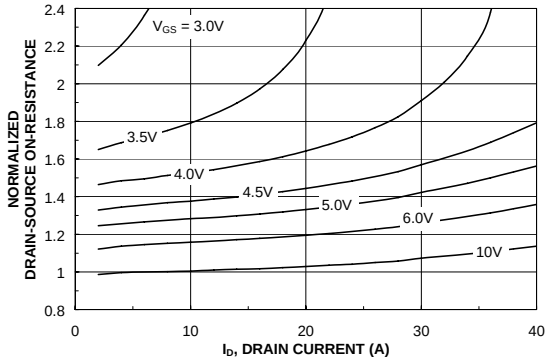



**Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.**

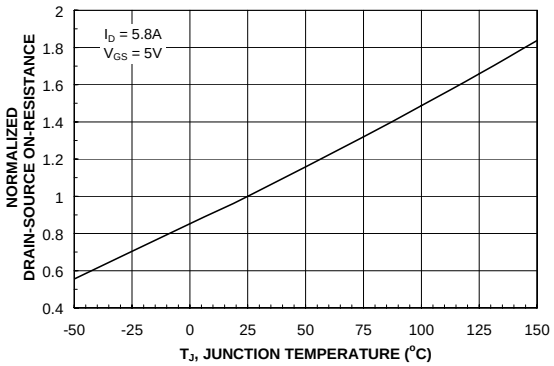



**Figure 3. On-Resistance Variation with Temperature.**

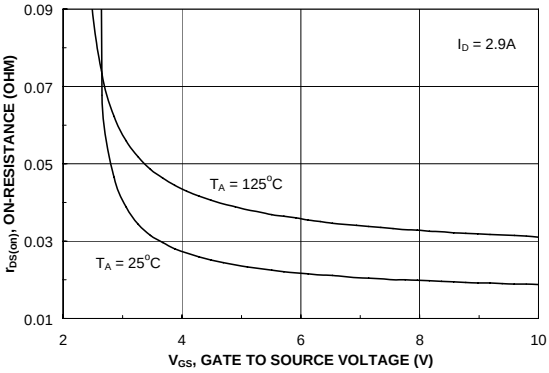



**Figure 4. On-Resistance Variation with Gate-to-Source Voltage.**

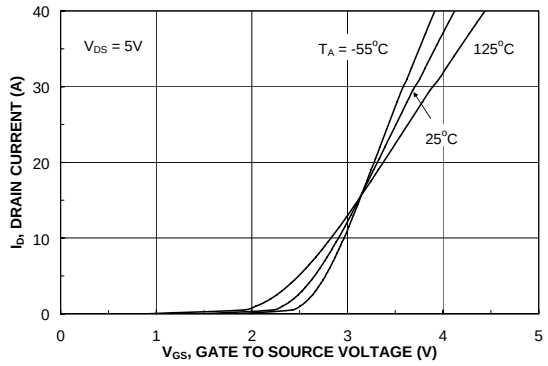



**Figure 5. Transfer Characteristics.**

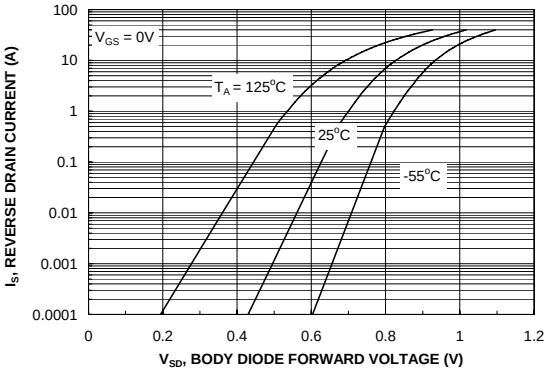



**Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.**

## Typical Characteristics

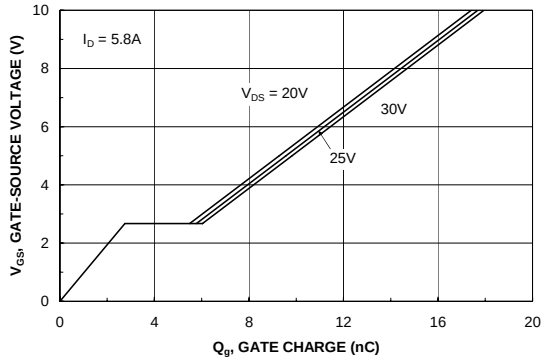



**Figure 7. Gate Charge Characteristics.**

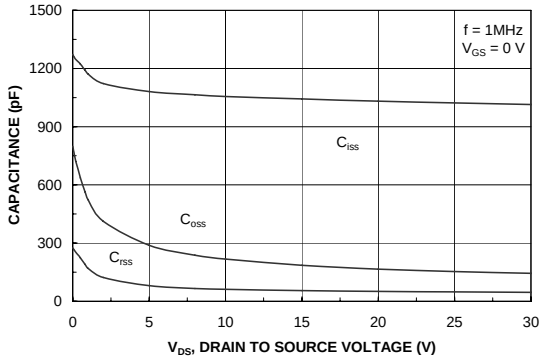



**Figure 8. Capacitance Characteristics.**

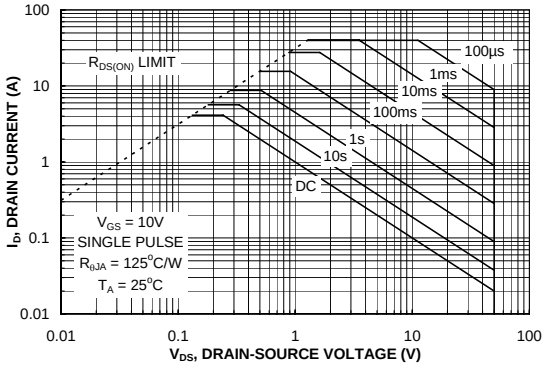



**Figure 9. Maximum Safe Operating Area.**

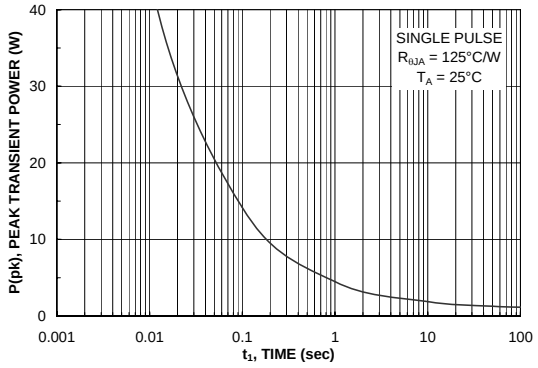



**Figure 10. Single Pulse Maximum UltraFET Dissipation.**

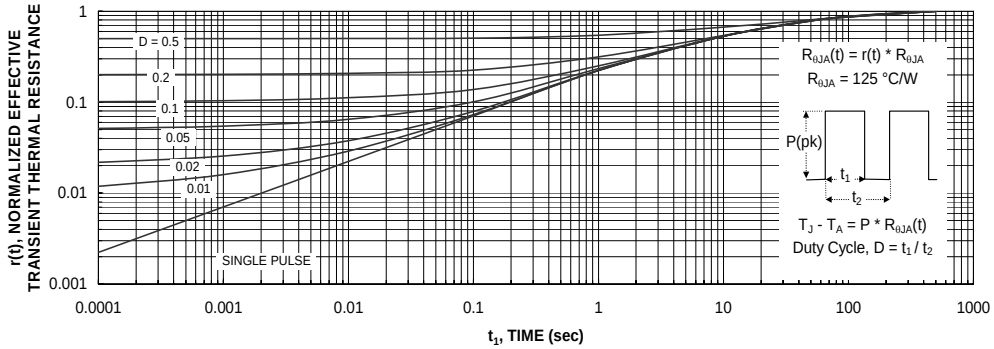



**Figure 11. Transient Thermal Response Curve.**

**Thermal characterization performed using the conditions described in Note 1c.**
**Transient thermal response will change depending on the circuit board design.**

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